2013 IEEE International Conference on Microelectronic Test Structures

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Table of Contents

SESSION 1: MEMS

Tuesday, March 26, 9:10-10:50
Co-Chairs: Kjell Jeppson, Chalmers University of Technology, Sweden
            Hiroaki Matsui, University of Tokyo, Japan

1.1 An Integrated CMOS-MEMS Probe having Two-Tips per Cantilever for Individual Contact Sensing and Kelvin Measurement with Two Cantilevers
Kota Hosaka, Satoshi Morishita, Isao Mori, Masanori Kubota, and Yoshio Mita
University of Tokyo, Japan

1.2 Characterization and Integration of Parylene as an Insulating Structural Layer for High Aspect Ratio Electroplated Copper Coils
University of Edinburgh, UK

1.3 Micromechanical Test Structures for the Characterization of Electroplated NiFe Cantilevers and their Viability for use in MEMS Switching Devices
G. Schiavone1, S. Smith1, J. Murray1, J.G. Terry1, M.P.Y. Desmulliez2, and A.J. Walton1
1University of Edinburgh, UK, 2Heriot-Watt University, UK

1.4 Investigation of Devices for In-Vivo Energy Harvesting through Blood-Flow-Like Excitation
Rosemary O’Keeffe, Nathan Jackson, Alan Mathewson, Kevin G. McCarthy
University College Cork, Ireland

1.5 A New Measurement Set-up to Investigate the Charge Trapping Phenomena in RF MEMS Packaged Switches
Marco Barbato, Valentina Giliberto, and Gaudenzio Meneghesso
University of Padova, Italy

SESSION 2: TSV and 3D

Tuesday, March 26, 11:20-12:20
Co-Chairs: Yosiho Mita, University of Tokyo, Japan
           Kevin McCarthy, University College Cork, Ireland

2.1 Test Structure and Analysis for Accurate RF-Characterization of Tungsten Through Silicon Via (TSV) Grounding Devices
Volker Blaschke and Hadi Jebory
TowerJazz, USA

2.2 Test Structures for Electrical Evaluation of High Aspect Ratio TSV Arrays Fabricated Using Planarised Sacrificial Photoresist
R. Zhang1, Y. Li1, J. Murray1, A. S. Bunting1, S. Smith1, C. C. Dunare1, J. T. M. Stevenson1, M.P. Desmulliez2, and A. J. Walton1
1University of Edinburgh, UK, 2Heriot-Watt University, UK

2.3 A Novel Silicon Interposer for Measuring Devices Requiring Complex Two-sided Contacting
Jaber Derakhshandeh, Negin Golshani, Loek A. Steenweg, Wim van der Vlist, and Lis K. Nanver
Delft University of Technology, The Netherlands

- iv -
SESSION 3: Capacitance

Tuesday, March 26, 13:50-15:10
Co-Chairs: Larg H. Weiland, PDF Solutions, USA
           Alain Toffoli, CEA-LETI, France

3.1 Characterization of Capacitance Mismatch Using Simple Difference Charge-Based Capacitance Measurement (DCBCM) Test Structure
Ken Sawada¹, Geert Van der Plas², Yuichi Miyamori³, Tetsuya Oishi⁴, Cherman Vladimir², Abdelkarim Mercha², Verkest Diederik², and Hiroaki Ammo⁴
¹Sony Corporation to IMEC, ²IMEC, Belgium
³Sony Semiconductor Corporation, Japan, ⁴Sony Corporation, Japan

3.2 Comparison of C-V Measurement Methods for RF-MEMS Capacitive Switches
Jiahui Wang, Cora Salm, and Jurriaan Schmitz
University of Twente, The Netherlands

3.3 Effective Channel Length Estimation Using Charge-Based Capacitance Measurement
Katsuhiro Tsuji and Kazuo Terada
Hiroshima City University, Japan

3.4 A New Ultra-Fast Single Pulse Technique (UFSP) for Channel Effective Mobility Evaluation in MOSFETs
Z. Ji¹, J. Gillbert², J. F. Zhang¹, and W. Zhang¹
¹Liverpool John Moores University, UK, ²Keithley Instruments, UK

SESSION 4: Noise and RF

Tuesday, March 26, 15:40-17:00
Co-Chairs: Hi-Deok Lee, Chungnam National University, Korea
           Tatsuya Ohguro, Toshiba Corporation

4.1 Optical High Frequency Test structure and Test Bench Definition for on Wafer Silicon Integrated Noise Source Characterization up to 110 GHz based on Germanium-on-Silicon Photodiode
S. Oeuvrard¹, ², J.-F. Lampin², G. Ducournau², L. Virot¹, ², J.M. Fedeli³, J.M. Hartmann³, F. Danneville³, Y. Morandini³, and D. Gloria³
¹STMicroelectronics, France, ²IEMN, France
³CEA LETI, France, ⁴DOLPHIN INTEGRATION, France

4.2 Measurements of SRAM Sensitivity against AC Power Noise with Effects of Device Variation
Takuya Sawada¹, Kumpai Yoshikawa¹, Hidehiro Takata², Koji Nii², and Makoto Nagata¹,³
¹Kobe University, Japan
²Renesas Electronics Corporation, Japan
³CREST, JST, Japan

4.3 On the Length of THRU Standard for TRL De-embedding on Si Substrate above 110 GHz
Hiroshima University, Japan

4.4 Evaluation of 1/f Noise Variability in the Subthreshold Region of MOSFETs
Hans Tuinhout and Adrie Zegers-van Duijnhoven
NXP Semiconductors, The Netherlands

- V -
SESSION 5: Variability and Yield

Wednesday, March 27, 9:00-10:20
Co-Chairs: Yoichi Tamaki, CASMAT, Japan
Hans Tuinhout, NXP Semiconductors, The Netherlands

5.1 Newly Developed Test-Element-Group for Detecting Soft Failures of the Low-Resistance-Element using Doubly Nesting Array
Shingo Sato, Hiroki Shinkawata, Atsushi Tsuda, Tomoaki Yoshizawa, and Takio Ohno
Renesas Electronics Corporation, Japan

5.2 New Methodology for Drain Current Local Variability Characterization using Y Function Method
L. Rahhal¹,2, A. Bajolet¹, C. Diouf¹,2, A. Cros¹, J. Rosa¹, N. Planes¹, and G. Ghibaudo²
¹STMicroelectronics, France
²IMEP-LAHC, France

5.3 A Novel BJT Structure for High-Performance Analog Circuit Applications
Seon-Man Hwang¹, Hyuk-Min Kwon¹, Jae-Hyung Jang¹, Ho-Young Kwak¹, Sung-Kyu Kwon¹,
Seung-Yong Sung¹, Jong-Kwan Shin¹, Jae-Nam Yu¹, In-Shik Han², Yi-Sun Chung², Jung-Hwan Lee²,
Ga-Won Lee¹, and Hi-Deok Lee¹
¹Chungnam National University, Korea
²MagnaChip Semiconductor, Korea

5.4 Reconsideration of the Threshold Voltage Variability Estimated with Pair Transistor Cell Array
Kazuo Terada, Naoya Higuchi, and Katsushiro Tsuji
Hiroshima City University, Japan

SESSION 6: Thermal and Power

Wednesday, March 27, 10:50-12:10
Co-Chairs: Satoshi Habu, Agilent Technologies Japan, Japan
Stewart Smith, University of Edinburgh, UK

6.1 Comparison of Electrical Techniques for Temperature Evaluation in Power MOS Transistors
A. Ferrara¹, P.G. Steeneken², K. Reimann², A. Heringa³, L. Yan¹, B.K. Boksteen¹, M. Swanenberg²,
G.E.J. Koops³, A.J. Scholten², R. Surdeanu², J. Schmitz¹, and R.J.E. Hueting¹
¹University of Twente, The Netherlands
²NXP Semiconductors, The Netherlands
³NXP Semiconductors, Belgium

6.2 Measurement and Investigation of Thermal Properties of the On-Chip Metallization for Integrated Power Technologies
Martin Pfoist¹, Cristian Boianceanu², Dan-Ionuţ Simon², and Sebastian Sosin²
¹Reutlingen University, Germany
²Infineon Technologies, Romania

6.3 Investigation on Safe Operating Area and ESD Robustness in a 60-V BCD Process with Different Deep P-Well Test Structures
Chia-Tsen Dai and Ming-Dou Ker
National Chiao-Tung University, Taiwan

6.4 A Test Structure for Analysis of Temperature Distribution in CMOS LSI with Sensing Device Array
T. Matsuda¹, H. Hanai¹, H. Iwata¹, D. Kondo¹, T. Hatakeyama¹, M. Ishizuka¹, and T. Ohzone²
¹Toyama Prefectural University, Japan
²Dawn Enterprise, Japan
SESSION 7: Parameter Extraction

Wednesday, March 27, 13:50-15:10
Co-Chairs: Luca Selmi, University of Udine, Italy
           Colin McAndrew, Freescale Semiconductor, USA

7.1 Analysis of Narrow Gate to Gate Space Dependence of MOS Gate-Source/Drain Capacitance by Using Contact-less and Drawn-out Source/Drain Test Structure
Yasuhisa Naruta and Shigetaka Kumashiro
Renesas Electronics Corporation, Japan

7.2 Three- and Four-Point Hamer-type MOSFET Parameter Extraction Methods Revisited
Kjell O. Jeppson
Chalmers University of Technology, Sweden

7.3 Die-to-Die and Within-Die Variation Extraction for Circuit Simulation with Surface-Potential Compact Model
Y. Ohnari, A.A. Khan, A. Dutta, M. Miura-Mattausch, and H. J. Mattausch
Hiroshima University, Japan

7.4 BSIM4 Parameter Extraction for Tri-gate Si Nanowire Transistors
Chika Tanaka, Masumi Saitoh, Kensuke Ota, and Toshinori Numata
Toshiba Corporation, Japan

SESSION 8: Emerging Technologies

Wednesday, March 27, 15:40-17:00
Co-Chairs: Anthony J. Walton, University of Edinburgh, UK
           Bill Verzi, Agilent Technologies, USA

8.1 Benchmarking of a Surface Potential Based Organic Thin-Film Transistor Model against \( \text{C}_{10} \)-DNTT High Performance Test Devices
Hiroshima University, Japan

8.2 Electrical and Mechanical Characterization of a Large-area Printed Organic Transistor Active Matrix with Floating-gate-based Non-uniformity Compensator
Tsuyoshi Sekitani, Tomoyuki Yokota, Takeyoshi Tokuhara, Naoya Take, and Takao Someya
University of Tokyo, Japan
ERATO, JST, Japan

8.3 Greek Cross Test Structures for Ink Jet Printed Thin Films
Elkin Diaz, Eloi Ramon, and Jordi Carrabina
Universitat Autònoma de Barcelona, Spain

8.4 Process Control Monitors for Individual Single-walled Carbon Nanotube Transistor Fabrication Processes
Kiran Chikkadi, Miroslav Haluska, Christofer Hierold, and Cosmin Roman
ETH Zurich, Switzerland
SESSION 9: Memory

Thursday, March 28, 9:00-10:20
Co-Chairs: Kazuo Terada, Hiroshima City University, Japan
Alexey Kovalgin, University of Twente, The Netherlands

9.1 Automatic Test Methodology to Optimize Operating Conditions and Reliability of Conductive Bridge RAM
A. Toffoli, E. Vianello, G. Molas, L. Perniola, B. De Salvo, and G. Reimbold
CEA-LETI, France

9.2 A Proper Approach to Characterize Retention-after-Cycling in 3D-Flash Devices
Fengying Qiao1, Antonio Arreghini2, Pieter Blomme2, Geert Van den bosch2, Liyang Pan1, Jun Xu1, and Jan Van Houdt2
1Tsinghua University, China
2IMEC, Belgium

9.3 A Novel Test Structure to Implement a Programmable Logic Array Using Split-Gate Flash Memory Cells
Henry Om’mani, Mandana Tadayoni, Nitya Thota, Ian Yue, and Nhan Do
Silicon Storage Technology, USA

9.4 On-wafer Integrated System for Fast Characterization and Parametric Test of New-Generation Non Volatile Memories
Erika Covi1, Alessandro Cabrini1, Loris Vendrame2, Luca Bortesi1, Roberto Gastaldi2, and Guido Torelli1
1University of Pavia, Italy
2Micron Semiconductor Italia, Italy

SESSION 10: Arrays and Ring Oscillators

Thursday, March 28, 10:40-12:00
Co-Chairs: Tsuyoshi Sekitani, University of Tokyo, Japan
Christopher Hess, PDF Solutions, USA

10.1 Tr Variance Evaluation induced by Probing Pressure and its Stress Extraction Methodology in 28nm High-K and Metal Gate process
Renesas Electronics Corporation, Japan

10.2 Efficient Technique for Si Validation of Level Shifters
Puneet Sharma1, Brad Smith2, Donald Hall2, Mike Nelson2, and Umesh Lohani1
1Freescale Semiconductor, India, 2Freescale Semiconductor, USA

10.3 Mosaic SRAM Cell TEGs with Intentionally-added Device Variability for Confirming the Ratio-less SRAM Operation
Hitoshi Okamura, Takahiko Saito, Hiroaki Goto, Masahiro Yamamoto, and Kazuyuki Nakamura
Kyushu Institute of Technology, Japan

10.4 Characterization and Simulation of NMOS Pass Transistor Reliability for FPGA Routing Circuits
Christopher S. Chen and Jeffrey T. Watt
Altera Corporation, USA